



Journal Name

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Li Dopant Inducing Moisture Sensitive Phase Degradation of All-inorganic CsPbI₂Br Perovskite

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Supplementary Information

Experiment Details

Materials: The CsI, PbI₂ and PbBr₂ were purchased from Alfa Aesar. The PMMA and DMF was purchased from Sigma-Aldrich. The HPbI_{3+x} (x=0.1-0.2) were prepared by mixing PbI₂ and 57% w/w hydroiodic acid (molar ratio 1:1.4) in DMF and then stirring for 2h.³⁵ The excess HI was used to ensure the complete conversion of PbI₂ into HPbI_{3+x}. The precipitates were recovered by evaporating the solutions at 70 °C. Finally, the resulting solid was centrifuged and washed four times with copious diethyl ether until supernatant turned to colorless. The collected powders were stored in oven at 50 °C.

Device preparation: The patterned TEC-15 FTO substrate was coated with a compact TiO₂ layer by spray pyrolysis using 0.2 M Ti(IV) bis (ethyl acetoacetate)-diisopropoxide in 1-butanol solution at 450 °C. The coated substrate was then annealed at 450 °C for one hour. The 0.5 M perovskite CsPbI₂Br in N,N-Dimethylformamide (DMF) was prepared by mixing stoichiometric CsI, HPbI_{3+x} and PbBr₂ with 2:1:1 molar ratio. Then the precursor solution was spun onto the c-TiO₂/FTO substrate at 3000 rpm with accelerating rate of 3000 rpm/s for 30 s, following by annealing at 150 °C for 4 minutes to form inorganic perovskite film. The TiO₂ coated substrates were subject to preheating at 70 °C in order to increase the surface coverage of the inorganic perovskite. PMMA (10mg/ml, chlorobenzene) was spun onto the perovskite film to form PMMA layer. Then the annealed perovskite films was spin-coated with a HTM layer consisting 0.1 M Spiro-MeOTAD, 0.035 M bis(trifluoromethane) sulfonamide lithium salt (Li-TFSi) and 0.12 M 4-tert-butylpyridine (tBP) in chlorobenzene/acetonitrile (10:1, v/v) solution at 4000 rpm for 20 s. Referring to the other work for PTAA³⁴, non-doping PTAA (10mg/ml in toluene) was spun onto the annealed perovskite. A 100-nm thick Ag layer was deposited by thermal evaporation.

Moisture stability evaluation: PMMA (10 mg/ml, chlorobenzene) was spun onto the perovskite film to form PMMA layer. The relative humidity level of the drybox was controlled by the entrance ratio of dry air in and moisture air. The a-CsPbI₂Br films were kept in the corresponding box to study phase changes.

Characterization: The crystal structures of the perovskite films were measured by X-ray diffraction (XRD, Shimadzu XRD-6100 diffractometer with Cu K α radiation). The absorption spectra of the perovskite films were characterized by a Cary-60 UV-vis spectrophotometer. The morphologies of the perovskite films were characterized using SEM (JEOL JSM-7800F Prime). The photocurrent-voltage (J-V) characteristic of perovskite solar cells was measured with a Keithley 2401 source meter with a scan rate of 0.05 V/s under simulated AM 1.5G illumination using Enlitech's 3A light source.

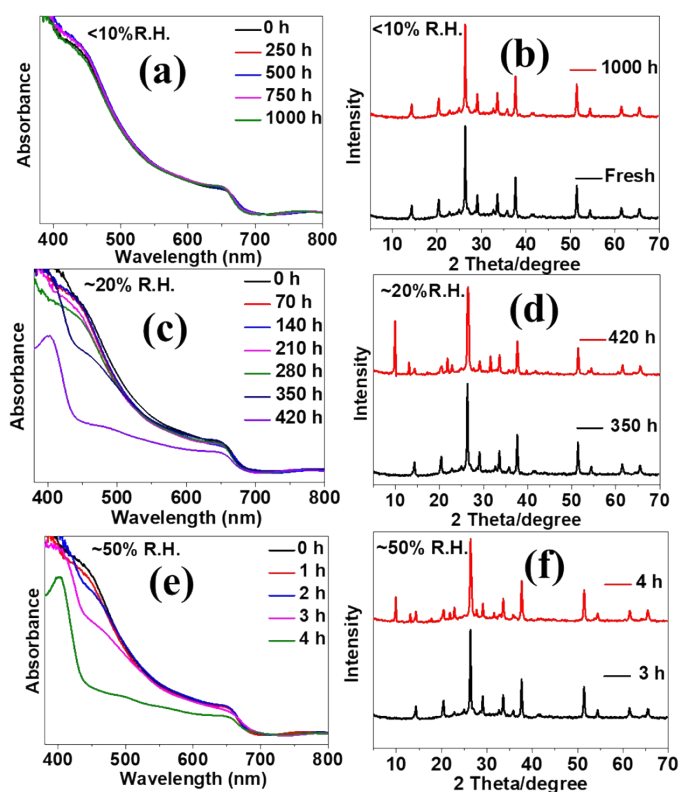


Fig. S1 (a, c, e) Evolution of UV-vis absorption and (b, d, f) XRD patterns of α -CsPbI₂Br films exposed to different R.H. of <10%, ~20%, ~50% and different exposure times.

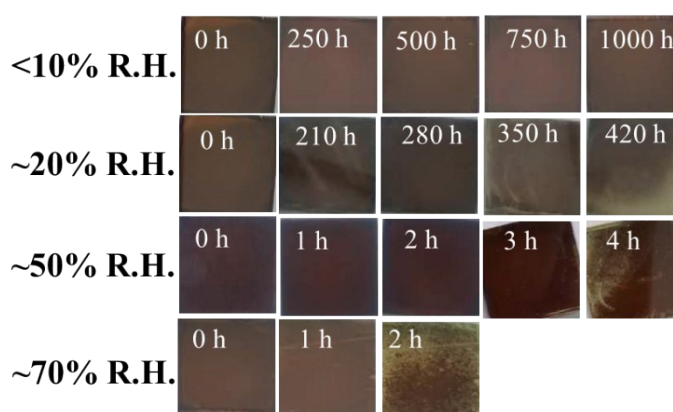


Fig. S2 Variation of color of the α -CsPbI₂Br films exposed to different R.H. of <10%, ~20%, ~50%, and ~70%.

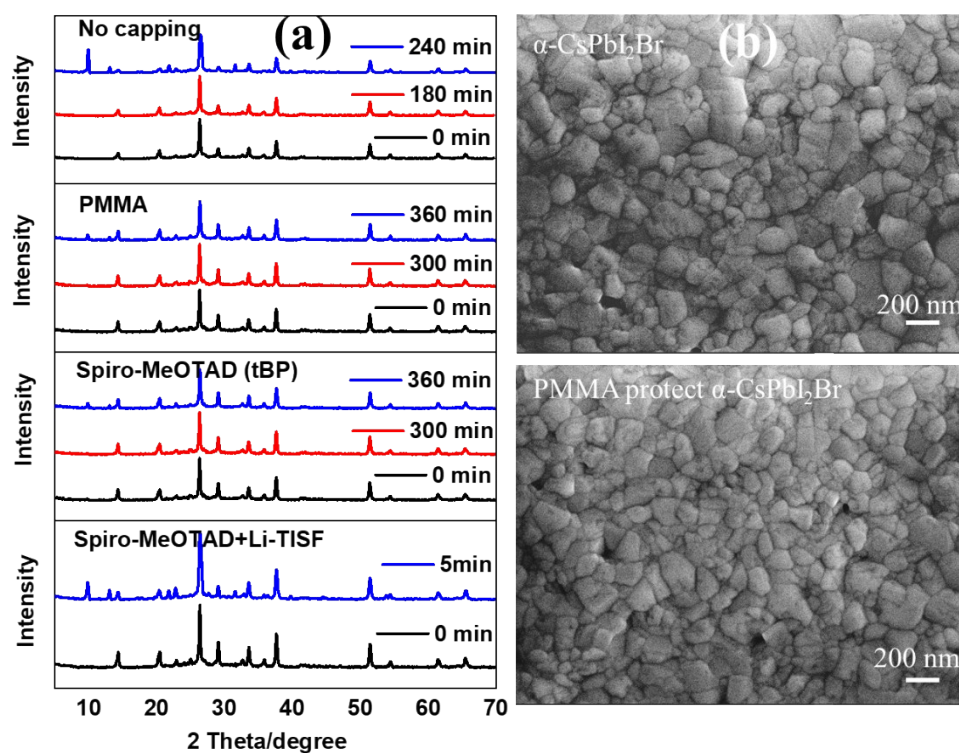


Fig. S3 (a) XRD patterns of CsPbI₂Br films with and without PMMA, Spiro-MeOTAD (tBP), and Spiro-MeOTAD+Li-TISF capping. (b) SEM images of α -CsPbI₂Br films (top) without PMMA capping and (bottom) with PMMA capping.

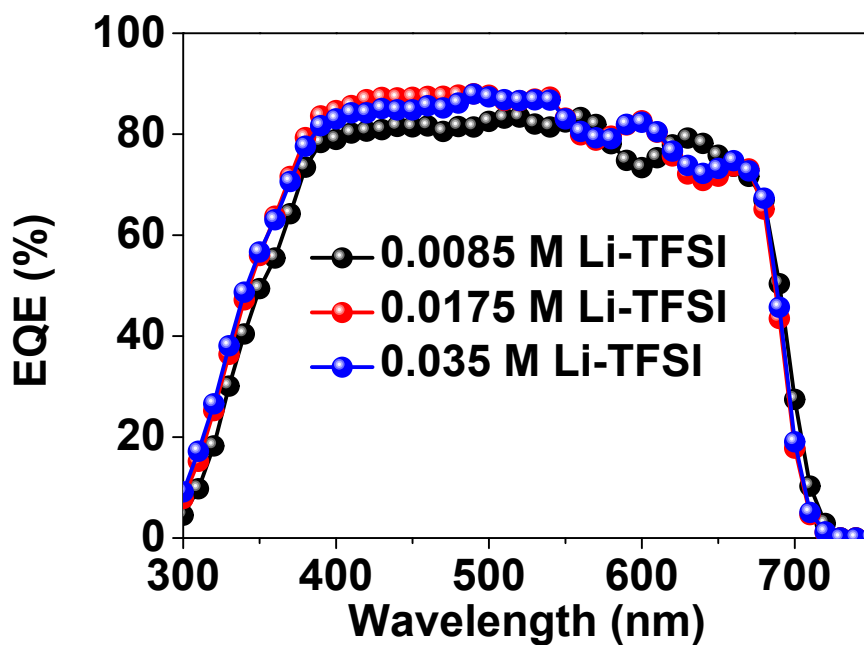


Fig. S4 IPCE of CsPbI₂Br PSCs based on Spiro-MeOTAD with 0.0085 M Li-TFSI, 0.0175 M Li-TFSI, and 0.035 M Li-TFSI doping.

Table S1. Photovoltaic parameters of CsPbI₂Br PSCs based on Spiro-MeOTAD with 0.0085 M Li-TFSI, 0.0175 M Li-TFSI, and 0.035 M Li-TFSI doping. The data were averaged from 32 devices.

	<i>J</i>_{sc} (mA·cm⁻²)	<i>V</i>_{oc} (V)	FF	PCE (%)
0.0085M	15.56 ± 0.13	1.04 ± 0.015	53 ± 3	8.57 ± 0.59
0.0175M	15.67 ± 0.1	1.044 ± 0.01	62.9 ± 1.8	10.3 ± 0.4
0.035M	15.7 ± 0.09	1.06 ± 0.01	72.35 ± 2.2	12.04 ± 0.37